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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/766,212	01/29/2004	Masaru Takaishi	AI 325	3347	
75	90 07/26/2005		EXAMINER		
RABIN & BERDO, P.C. 1101 14 Street, N.W., Suite 500			TOLEDO, FERNANDO L		
Washington, D			ART UNIT	PAPER NUMBER	
-			2823		
			DATE MAILED: 07/26/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		10/766,212	TAKAISHI, MASARU			
		Examiner	Art Unit			
		Fernando L. Toledo	2823			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
THE MA - Extension after SIX - , if the peri - if NO peri - Failure to Any reply	TENED STATUTORY PERIOD FOR REPLY ILING DATE OF THIS COMMUNICATION. It is of time may be available under the provisions of 37 CFR 1.13 (6) MONTHS from the mailing date of this communication. Of for reply specified above is less than thirty (30) days, a reply iod for reply is specified above, the maximum statutory period with reply within the set or extended period for reply will, by statute, received by the Office later than three months after the mailing atent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be within the statutory minimum of thirty (30) Il apply and will expire SIX (6) MONTHS from the application to become ABANDO	e timely filed days will be considered timely. om the mailing date of this communication. NED (35 U.S.C. § 133).			
Status	•					
1)⊠ Re	esponsive to communication(s) filed on 29 Ja	nuary 2004.				
2a) <u></u> ⊤h	This action is FINAL . 2b)⊠ This action is non-final.					
3) □ Sir	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
clo	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition	of Claims	•				
4)⊠ Cla 4a) 5)□ Cla 6)⊠ Cla 7)□ Cla	aim(s) 1-9 is/are pending in the application. Of the above claim(s) is/are withdraw aim(s) is/are allowed. aim(s) 1-9 is/are rejected. aim(s) is/are objected to. aim(s) are subject to restriction and/or					
Application	Papers					
10)⊠ The Ap Re	e specification is objected to by the Examiner of drawing(s) filed on 29 January 2004 is/are: plicant may not request that any objection to the oplacement drawing sheet(s) including the correction of the open of declaration is objected to by the Examiner.	a)⊠ accepted or b)⊡ object lrawing(s) be held in abeyance. S on is required if the drawing(s) is	See 37 CFR 1.85(a). objected to. See 37 CFR 1.121(d).			
Priority und	ler 35 U.S.C. § 119					
12)⊠ Ac⊦ a)⊠ A 1.[2.[3.[knowledgment is made of a claim for foreign All b) Some * c) None of: Certified copies of the priority documents Certified copies of the priority documents Copies of the certified copies of the priori application from the International Bureau the attached detailed Office action for a list of	have been received. have been received in Applic ty documents have been rece (PCT Rule 17.2(a)).	ation No vived in this National Stage			
Attachment(s)	•					
1) Notice of 2) Notice of 3) Information	References Cited (PTO-892) Draftsperson's Patent Drawing Review (PTO-948) on Disclosure Statement(s) (PTO-1449 or PTO/SB/08) o(s)/Mail Date 1/21/04, 4/23/04, 6/21/05	4) Interview Summ Paper No(s)/Mai 5) Notice of Informa 6) Other:	ary (PTO-413) Date al Patent Application (PTO-152)			

DETAILED ACTION

Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1 9 are rejected under 35 U.S.C. 102(b) as being anticipated by Hsu et al. (U. S. Patent 6,143,645 A).
- 4. In re claim 1, Hsu, in the U. S. Patent 6,143,645 A; figures 1-3 and related text, discloses forming a silicon-containing thin film 500 in a region having a predetermined area including the inner surface of the contact hole on the surface of the semiconductor substrate; forming an aluminum-containing thin film 520 on the surface of the semiconductor substrate on which the silicon-containing thin film is formed; and heating the semiconductor substrate on which the aluminum-containing thin film is formed to such a temperature as to cause silicon to diffuse with respect to aluminum (Column 4, Lines 15-30 and Figure 3).
- 5. In re claim 2, Hsu discloses wherein the step of forming an aluminum-containing thin film and the step of heating the semiconductor substrate is carried out simultaneously (Column 4, Lines 15-30).

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6. In re claim 3, Hsu discloses wherein the step of heating the semiconductor substrate is carried out after completing the step of forming an aluminum-containing thin film (Figure 3).

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- 7. In re claim 4, Hsu discloses wherein the step of forming a silicon-containing thin film in the region having the predetermined area includes the step of: forming a silicon-containing thin film in a region larger than the predetermined area; and removing the silicon-containing thin film so that the area of the silicon-containing thin film can become the abovementioned predetermined area (Column 7, Lines 16 – 19).
- 8. In re claim 5, Hsu discloses wherein the step of removing the silicon-containing thin film includes a step of removing the silicon-containing thin film using a mask having a predetermined pattern (it is conventional in the art that to form a plug a mask must be used to avoid etching the plug).
- 9. In re claim 6, Hsu discloses wherein the step of removing the silicon-containing thin film includes a step of removing the silicon-containing thin film by etching (it is well-known in the art and conventional to remove unwanted portions by etching).
- In re claim 7, Hsu discloses wherein the predetermined area is not more than 99% of the 10. area of the aluminum-containing thin film formed in the step of forming the aluminum thin film (Figure 2).
- 11. In re claim 8, Hsu discloses wherein the semiconductor substrate is provided with several cells each including the contact hole, and the ratio of the amount of silicon contained in the silicon-containing thin film formed in the region having the predetermined area per unit cell to the amount of aluminum supplied to a unit cell in the step of forming the aluminum thin film is not less than 0.1% and not more than 2% by atomic ratio (Figure 3).

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12. In re claim 9, Hsu discloses wherein the step of heating the semiconductor substrate

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includes a step of heating the semiconductor substrate to 380°C - 570°C (Column 4, Lines 15 -

30).

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Fernando L. Toledo whose telephone number is 571-272-1867.

The examiner can normally be reached on Mon-Thu 7am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

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system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Fernando L. Toledo

Examiner

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flt

23 July 2005